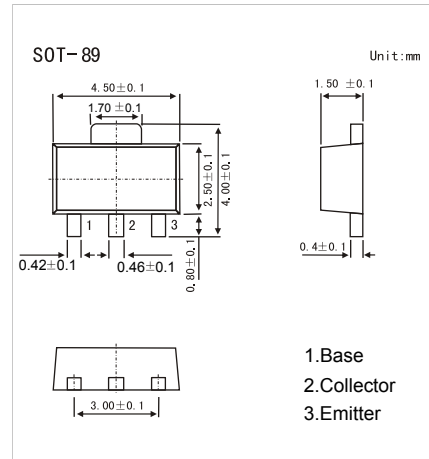


PNP Transistors

2SB1424

■ Features

- Excellent DC current gain
- Low collector-emitter saturation voltage
- Complementary to 2SD2150



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-20	V
Collector - Emitter Voltage	V _{CEO}	-20	
Emitter - Base Voltage	V _{EB0}	-6	
Collector Current - Continuous	I _C	-3	A
Collector Power Dissipation	P _C	500	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	250	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 uA, I _E =0	-20			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, I _B =0	-20			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 uA, I _C =0	-6			
Collector-base cut-off current	I _{CB0}	V _{CB} = -20V, I _E =0			-0.1	uA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2 A, I _B =-100 mA			-0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-2 A, I _B =-100 mA			-1.2	
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -100 mA	120		390	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz		35		pF
Transition frequency	f _T	V _{CE} = -2V, I _C = -500 mA, f=100MHz		240		MHz

■ Classification of h_{FE}

Type	2SB1424-Q	2SB1424-R
Range	120-270	180-390
Marking	AEQ	AER



炬芯微
XUANXINWEI

SMD Type

Transistors

PNP Transistors

2SB1424

Typical Characteristics

